

**Description**

The SX40P02D uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

**General Features**

$V_{DS} = -20V$   $I_D = -40A$

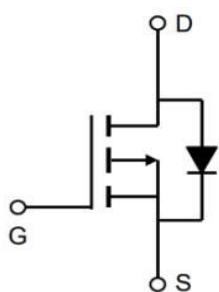
$R_{DS(ON)}$  Type:  $12m\Omega$  @  $V_{GS}=-4.5V$

**Application**

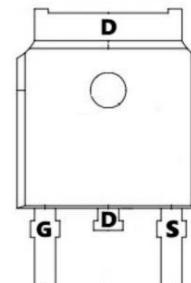
Battery protection

Load switch

Uninterruptible power supply



TO-252-3L

**Absolute Maximum Ratings ( $T_c=25^\circ C$  unless otherwise noted)**

| Symbol                 | Parameter  | Rating     | Units |
|------------------------|--|------------|-------|
| $V_{DS}$               | Drain-Source Voltage                             | -20        | V     |
| $V_{GS}$               | Gate-Source Voltage                              | $\pm 12$   | V     |
| $I_D @ T_c=25^\circ C$ | Continuous Drain Current, $V_{GS} @ -4.5V^1$     | -40        | A     |
| $I_D @ T_c=70^\circ C$ | Continuous Drain Current, $V_{GS} @ -4.5V^1$     | -35        | A     |
| $IdM$                  | Pulsed Drain Current <sup>2</sup>                | -160       | A     |
| $P_D @ T_c=25^\circ C$ | Total Power Dissipation <sup>3</sup>             | 2.5        | W     |
| $P_D @ T_c=70^\circ C$ | Total Power Dissipation <sup>3</sup>             | 1.6        | W     |
| $T_{STG}$              | Storage Temperature Range                        | -55 to 150 | °C    |
| $T_J$                  | Operating Junction Temperature Range             | -55 to 150 | °C    |
| $R_{eJA}$              | Thermal Resistance Junction-Ambient <sup>1</sup> | 65.5       | °C/W  |
| $R_{eJC}$              | Thermal Resistance Junction-Case <sup>1</sup>    | 24         | °C/W  |

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

| Symbol                     | Parameter                                      | Conditions   | Min. | Typ.   | Max.      | Unit                       |
|----------------------------|--|--|------|--------|-----------|----------------------------|
| BVDSS                      | Drain-Source Breakdown Voltage                 | $V_{GS}=0\text{V}$ , $I_D=-250\mu\text{A}$   | -20  | -23    | ---       | V                          |
| $\Delta BVDSS/\Delta T_J$  | $BV_{DSS}$ Temperature Coefficient             | Reference to $25^\circ\text{C}$ , $I_D=-1\text{mA}$                                | ---  | -0.012 | ---       | $\text{V}/^\circ\text{C}$  |
| RDS(ON)                    | Static Drain-Source On-Resistance <sup>2</sup> | $V_{GS}=-4.5\text{V}$ , $I_D=-20\text{A}$  | ---  | 12     | 20        | $\text{m}\Omega$           |
| RDS(ON)                    | Static Drain-Source On-Resistance <sup>2</sup> | $V_{GS}=-2.5\text{V}$ , $I_D=-10\text{A}$  | ---  | 22     | 28        |                            |
| VGS(th)                    | Gate Threshold Voltage                         | $V_{GS}=V_{DS}$ , $I_D=-250\mu\text{A}$  | -0.5 | -0.6   | -1.2      | V                          |
| $\Delta V_{GS(\text{th})}$ | $V_{GS(\text{th})}$ Temperature Coefficient    |  | ---  | 2.94   | ---       | $\text{mV}/^\circ\text{C}$ |
| IDSS                       | Drain-Source Leakage Current                   | $V_{DS}=-20\text{V}$ , $V_{GS}=0\text{V}$ , $T_J=25^\circ\text{C}$                 | ---  | ---    | 1         | $\mu\text{A}$              |
| IGSS                       | Gate-Source Leakage Current                    | $V_{GS}=\pm 12\text{V}$ , $V_{DS}=0\text{V}$                                       | ---  | ---    | $\pm 100$ | nA                         |
| Qg                         | Total Gate Charge (-4.5V)                      | $V_{DS}=-10\text{V}$ , $V_{GS}=-4.5\text{V}$ , $I_D=-6\text{A}$                    | ---  | 15.3   | ---       | nC                         |
| Qgs                        | Gate-Source Charge                             |  | ---  | 2.2    | ---       |                            |
| Qgd                        | Gate-Drain Charge                              |  | ---  | 4.4    | ---       |                            |
| Td(on)                     | Turn-On Delay Time                             | $V_{DD}=-10\text{V}$ , $V_{GS}=-4.5\text{V}$ , $R_G=3.3\Omega$ , $I_D=-10\text{A}$ | ---  | 10     | ---       | ns                         |
| Tr                         | Rise Time                                      |  | ---  | 31     | ---       |                            |
| Td(off)                    | Turn-Off Delay Time                            |  | ---  | 28     | ---       |                            |
| Tf                         | Fall Time                                      |  | ---  | 8      | ---       |                            |
| Ciss                       | Input Capacitance                              | $V_{DS}=-10\text{V}$ , $V_{GS}=0\text{V}$ , $f=1\text{MHz}$                        | ---  | 2000   | ---       | pF                         |
| Coss                       | Output Capacitance                             |  | ---  | 242    | ---       |                            |
| Crss                       | Reverse Transfer Capacitance                   |  | ---  | 231    | ---       |                            |
| IS                         | Continuous Source Current <sup>1,4</sup>       | $V_G=V_D=0\text{V}$ , Force Current  | ---  | ---    | -20       | A                          |
| ISM                        | Pulsed Source Current <sup>2,4</sup>           |  | ---  | ---    | -48       | A                          |
| VSD                        | Diode Forward Voltage <sup>2</sup>             | $V_{GS}=0\text{V}$ , $I_S=-1\text{A}$ , $T_J=25^\circ\text{C}$                     | ---  | ---    | -1.2      | V                          |

**Note :**

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3、The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4、The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

## Typical Characteristics

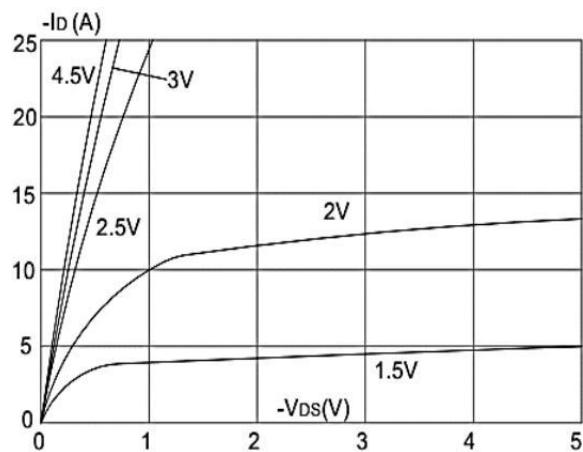


Figure 1: Output Characteristics

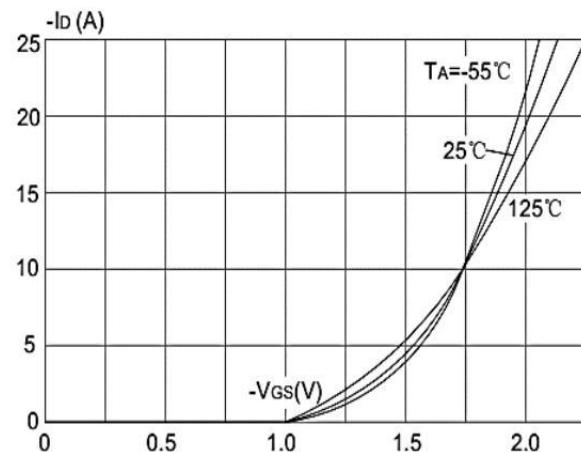


Figure 2: Typical Transfer Characteristics

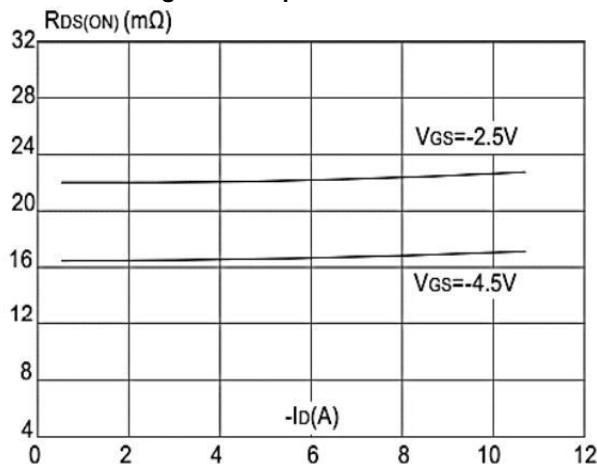


Figure 3: On-resistance vs. Drain Current

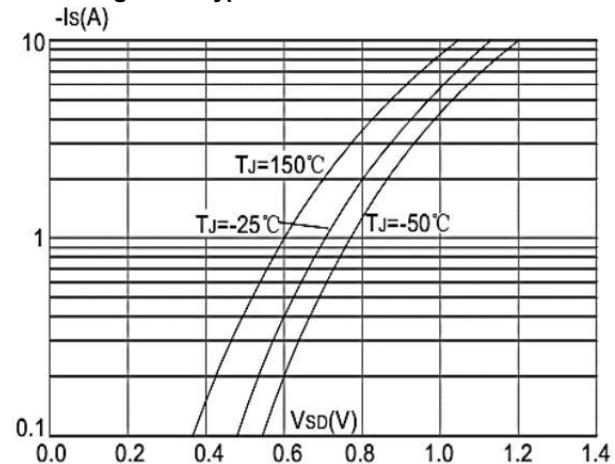


Figure 4: Body Diode Characteristics

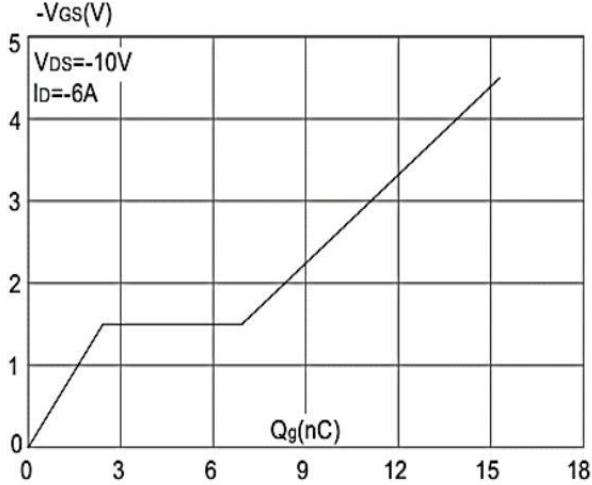


Figure 5: Gate Charge Characteristics

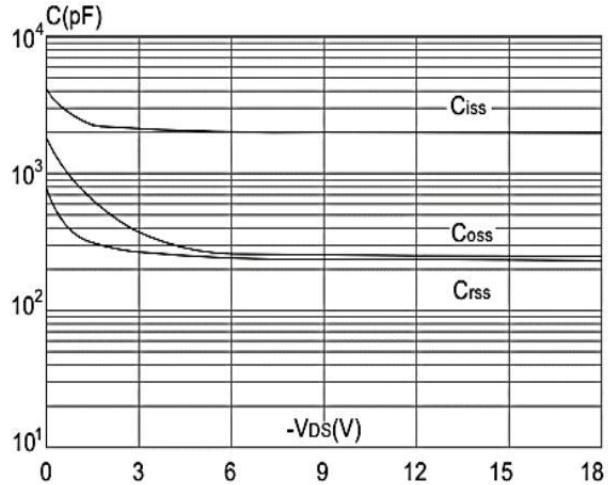


Figure 6: Capacitance Characteristics

## Typical Characteristics

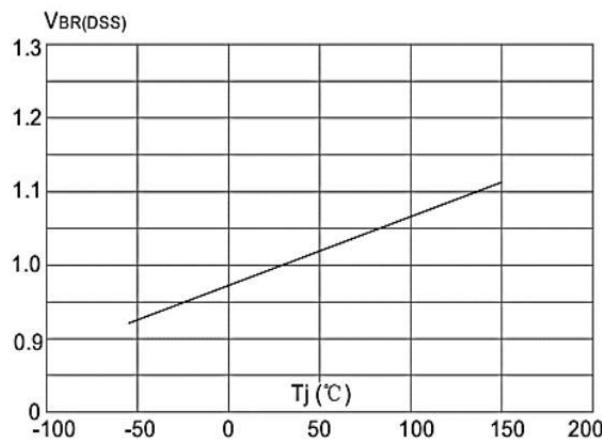


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

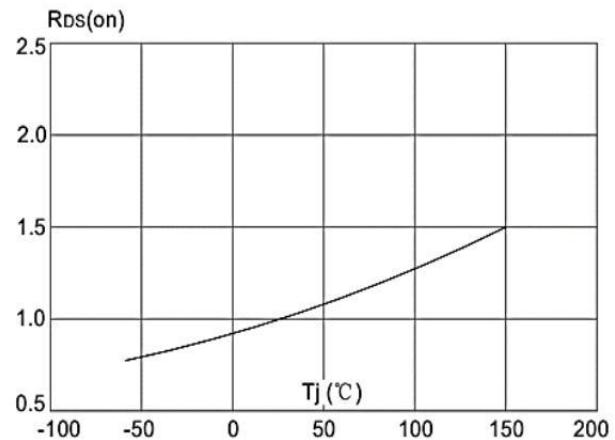


Figure 8: Normalized on Resistance vs. Junction Temperature

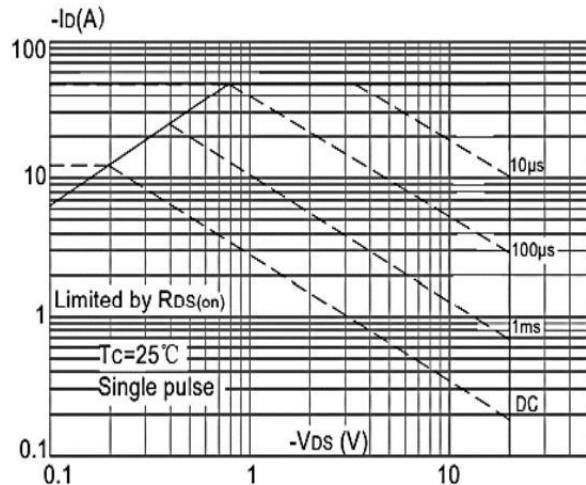


Figure 9: Maximum Safe Operating Area

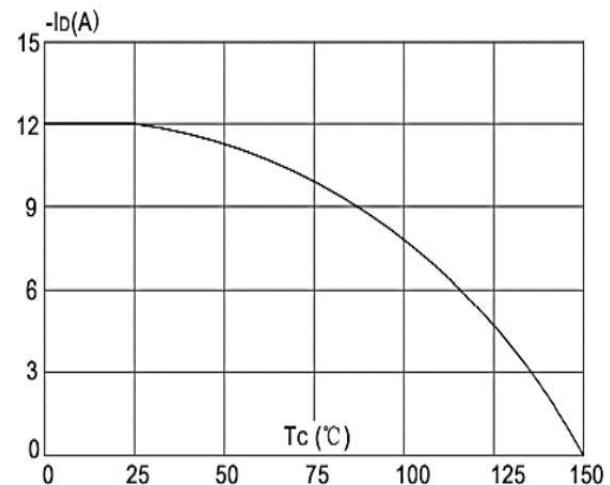


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

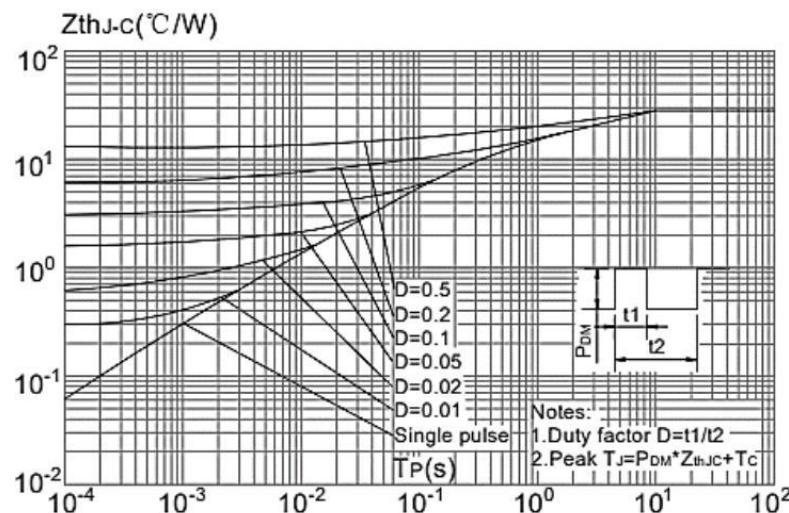
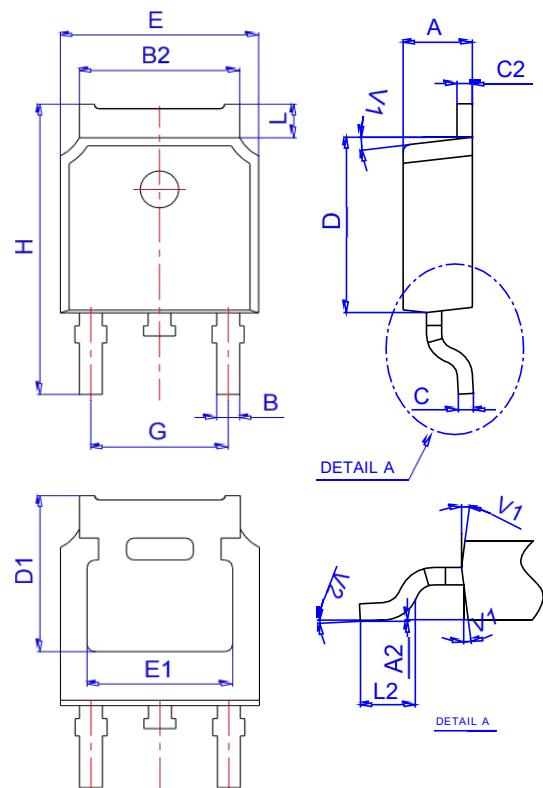


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

## Package Mechanical Data: TO-252-3L



| Ref. | Dimensions  |      |       |          |      |       |
|------|-------------|------|-------|----------|------|-------|
|      | Millimeters |      |       | Inches   |      |       |
|      | Min.        | Typ. | Max.  | Min.     | Typ. | Max.  |
| A    | 2.10        |      | 2.50  | 0.083    |      | 0.098 |
| A2   | 0           |      | 0.10  | 0        |      | 0.004 |
| B    | 0.66        |      | 0.86  | 0.026    |      | 0.034 |
| B2   | 5.18        |      | 5.48  | 0.202    |      | 0.216 |
| C    | 0.40        |      | 0.60  | 0.016    |      | 0.024 |
| C2   | 0.44        |      | 0.58  | 0.017    |      | 0.023 |
| D    | 5.90        |      | 6.30  | 0.232    |      | 0.248 |
| D1   | 5.30REF     |      |       | 0.209REF |      |       |
| E    | 6.40        |      | 6.80  | 0.252    |      | 0.268 |
| E1   | 4.63        |      |       | 0.182    |      |       |
| G    | 4.47        |      | 4.67  | 0.176    |      | 0.184 |
| H    | 9.50        |      | 10.70 | 0.374    |      | 0.421 |
| L    | 1.09        |      | 1.21  | 0.043    |      | 0.048 |
| L2   | 1.35        |      | 1.65  | 0.053    |      | 0.065 |
| V1   |             | 7°   |       |          | 7°   |       |
| V2   | 0°          |      | 6°    | 0°       |      | 6°    |

### Package Marking and Ordering Information

| Product ID | Pack      | Marking | Qty(PCS) |
|------------|-----------|---------|----------|
| TAPING     | TO-252-3L |         | 2500     |